

Docket No.: 005918 USA/FPS/MMCS/APC

PATENT/OFFICIAL

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

SHANMUGASUNDRAM et al.

Serial No. 09/943,955

: Group Art Unit: 1765

Filed: August 31, 2001

: Examiner: Lynette T. Umez Eronini

For: FEEDBACK CONTROL OF A CHEMICAL MECHANICAL POLISHING DEVICE
PROVIDING MANIPULATION OF REMOVAL RATE PROFILES

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This submission does not constitute a representation that a search has been made or that no better art exists and does not constitute an admission or representation that any of the listed documents is material or constitutes prior art. If it should be determined that any of the listed documents does not constitute prior art under the United States law, Applicants reserve the right

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Serial No. 09/943,955

to present to the Office the relevant facts and law regarding the appropriate status of such document.

Please charge the fee of \$180.00 under 37 CFR 1.17(p) to Deposit Account No. 08-0219.

The Commissioner is hereby authorized to charge any additional fees that may be required for this submission, or credit any overpayment to deposit account no. 08-0219.

Respectfully submitted,

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Date: 8/11/04

**INFORMATION DISCLOSURE
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(PTO-1449)**

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SERIAL NO.
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APPLICANT
SHANMUGASUNDRAM et al.

FILING DATE
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1765




U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
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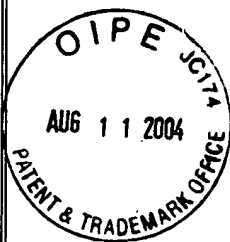
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DATE CONSIDERED

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 005918 USA/ FPS/MMCS/APC		SERIAL NO. 09/943,955	
				APPLICANT SHANMUGASUNDRAM et al.			
				FILING DATE August 31, 2001		GROUP 1765	
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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
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